

Evidence for intrinsic magnetic scatterers in the topological semimetal $(\text{Bi}_2)_5(\text{Bi}_2\text{Se}_3)_7$

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We report the synthesis and characterization of high-quality thin films of the topological semimetal $(\text{Bi}_2)_5(\text{Bi}_2\text{Se}_3)_7$. [1,2] Cryogenic magneto-transport experiments reveal strong metallic character and spin-orbit coupling in the films. By studying the temperature dependence of the electrical resistance of the topological semimetal, we observe a pronounced Kondo effect which points towards the presence of magnetic scatterers. [3,4] With the aid of density functional theory calculations we identify Bi vacancies as intrinsic magnetic scatterers in this topological semimetal.

References

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Figures

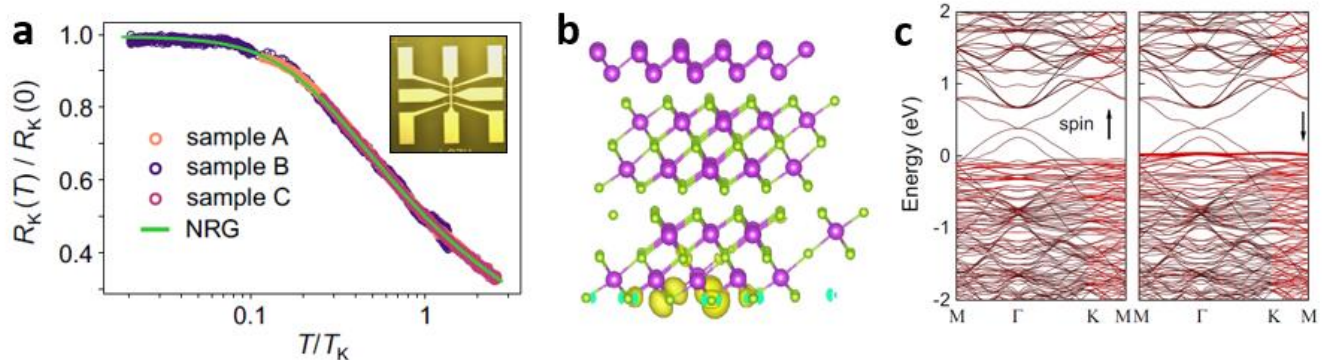


Figure 1: (a) Normalized Kondo resistivity as a function of temperature (normalized by the Kondo temperature) for samples A, B and C (open circles) together with the universal functional predicted by NRG calculations (green line). [4] Example device as inset image. (b) Atomic structure of a $\text{Bi}_2/(\text{Bi}_2\text{Se}_3)_2$ stack with a Bi vacancy in the bottom Bi_2Se_3 layer. The band-decomposed charge densities in the energy range between -0.02 and 0.03 eV are also shown in yellow. (c) Projected band structures of the system, for spin-up and spin-down electrons. The red lines correspond to the contributions from the 4p-Se orbitals around the Bi vacancy.